



Description

The HSM3107 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

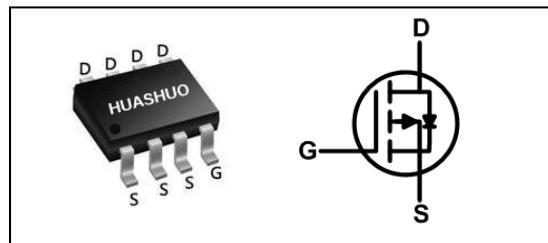
The HSM3107 meet the RoHS and Green Product requirement with full function reliability approved.

- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	-30	V
$R_{DS(ON),typ}$	42	mΩ
I_D	-5	A

SOP8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-5	A
$I_D @ T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-4	A
I_{DM}	Pulsed Drain Current ²	-20	A
EAS	Single Pulse Avalanche Energy ³	11.3	mJ
I_{AS}	Avalanche Current	15	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation ⁴	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	55	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$, $I_{\text{D}}=-250\mu\text{A}$	-30	---	---	V
$\Delta \text{BV}_{\text{DSS}}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_{\text{D}}=-1\text{mA}$	---	-0.02	---	$\text{V}/^\circ\text{C}$
$R_{\text{DS}(\text{ON})}$	Static Drain-Source On-Resistance ²	$V_{\text{GS}}=-10\text{V}$, $I_{\text{D}}=-4\text{A}$	---	42	62	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}$, $I_{\text{D}}=-2\text{A}$	---	62	90	
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{GS}}=V_{\text{DS}}$, $I_{\text{D}}=-250\mu\text{A}$	-1.0	---	-2.5	V
$\Delta V_{\text{GS}(\text{th})}$	$V_{\text{GS}(\text{th})}$ Temperature Coefficient		---	4.32	---	$\text{mV}/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{\text{DS}}=-24\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	-1	uA
		$V_{\text{DS}}=-24\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=55^\circ\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{\text{GS}}=\pm 20\text{V}$, $V_{\text{DS}}=0\text{V}$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{\text{DS}}=-5\text{V}$, $I_{\text{D}}=-4\text{A}$	---	5.5	---	S
R_g	Gate Resistance	$V_{\text{DS}}=0\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	24	---	Ω
Q_g	Total Gate Charge (-4.5V)	$V_{\text{DS}}=-20\text{V}$, $V_{\text{GS}}=-4.5\text{V}$, $I_{\text{D}}=-4\text{A}$	---	5.22	---	nC
Q_{gs}	Gate-Source Charge		---	1.25	---	
Q_{gd}	Gate-Drain Charge		---	2.3	---	
$T_{\text{d}(\text{on})}$	Turn-On Delay Time	$V_{\text{DD}}=-15\text{V}$, $V_{\text{GS}}=-10\text{V}$, $R_{\text{G}}=3.3\Omega$ $I_{\text{D}}=-1\text{A}$	---	18.4	---	ns
T_r	Rise Time		---	11.4	---	
$T_{\text{d}(\text{off})}$	Turn-Off Delay Time		---	39.4	---	
T_f	Fall Time		---	5.2	---	
C_{iss}	Input Capacitance	$V_{\text{DS}}=-15\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	463	---	pF
C_{oss}	Output Capacitance		---	82	---	
C_{rss}	Reverse Transfer Capacitance		---	68	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_s	Continuous Source Current ^{1,5}	$V_G=V_D=0\text{V}$, Force Current	---	---	-5	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	-20	A
V_{SD}	Diode Forward Voltage ²	$V_{\text{GS}}=0\text{V}$, $I_s=-1\text{A}$, $T_J=25^\circ\text{C}$	---	---	-1	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{\text{DD}}=-25\text{V}$, $V_{\text{GS}}=-10\text{V}$, $L=0.1\text{mH}$, $I_{\text{AS}}=-15\text{A}$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_{D} and I_{DM} , in real applications , should be limited by total power dissipation.



HUASHUO
SEMICONDUCTOR

HSM3107

Typical Characteristics

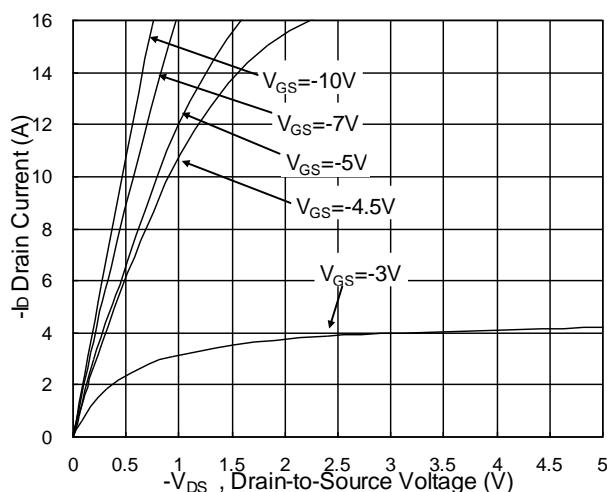


Fig.1 Typical Output Characteristics

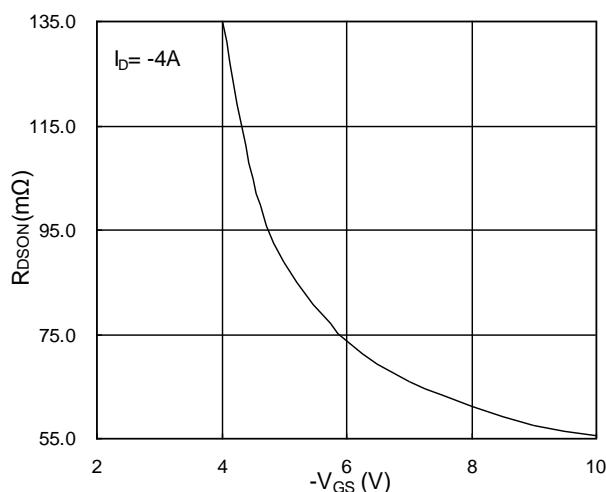


Fig.2 On-Resistance vs. G-S Voltage

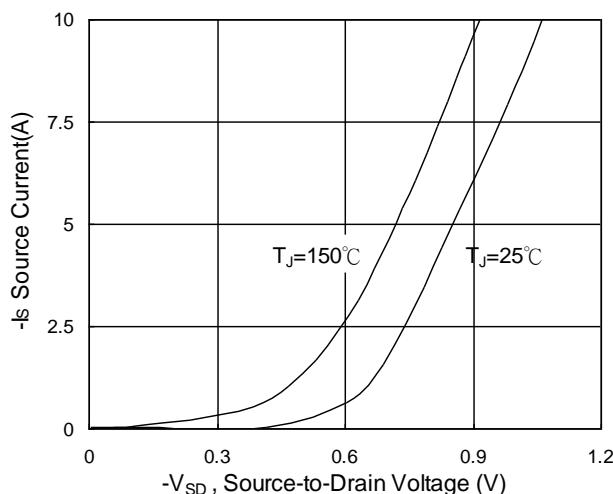


Fig.3 Forward Characteristics of Reverse

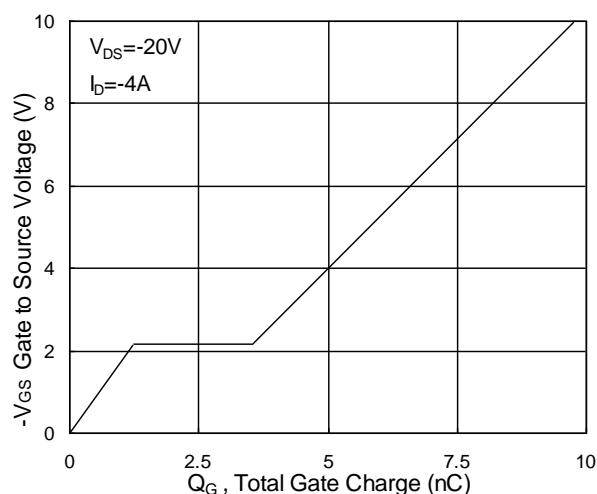


Fig.4 Gate-Charge Characteristics

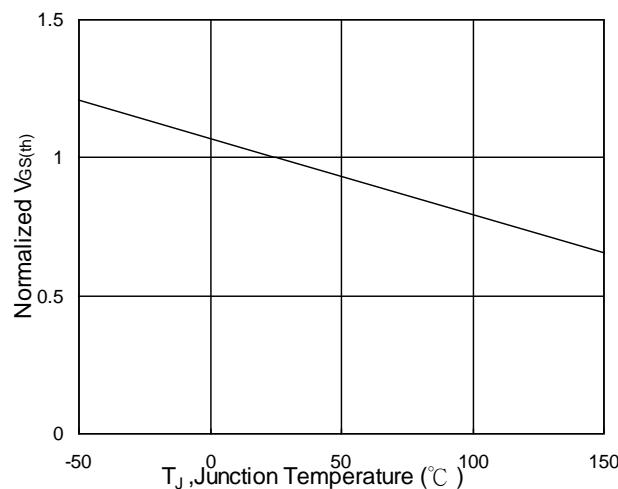


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

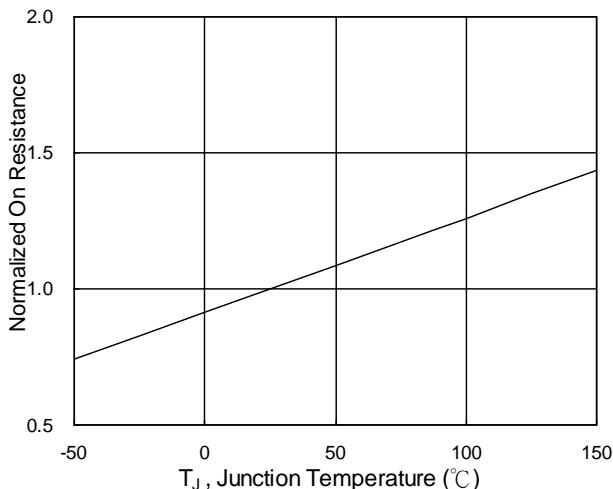


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

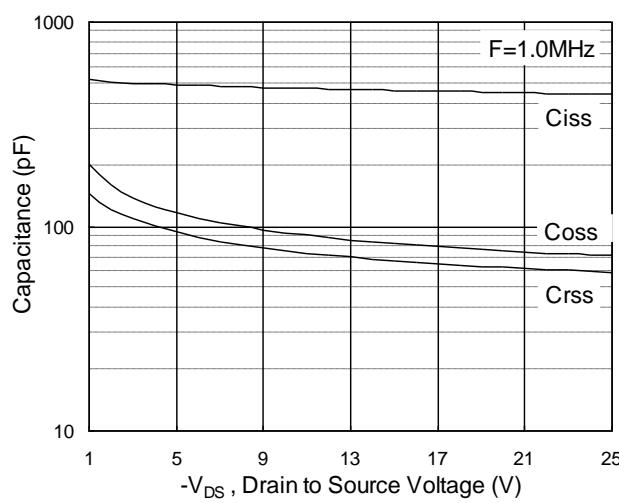


Fig.7 Capacitance

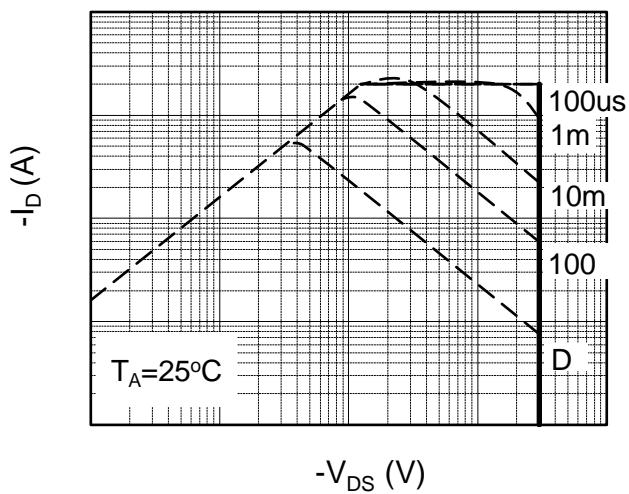


Fig.8 Safe Operating Area

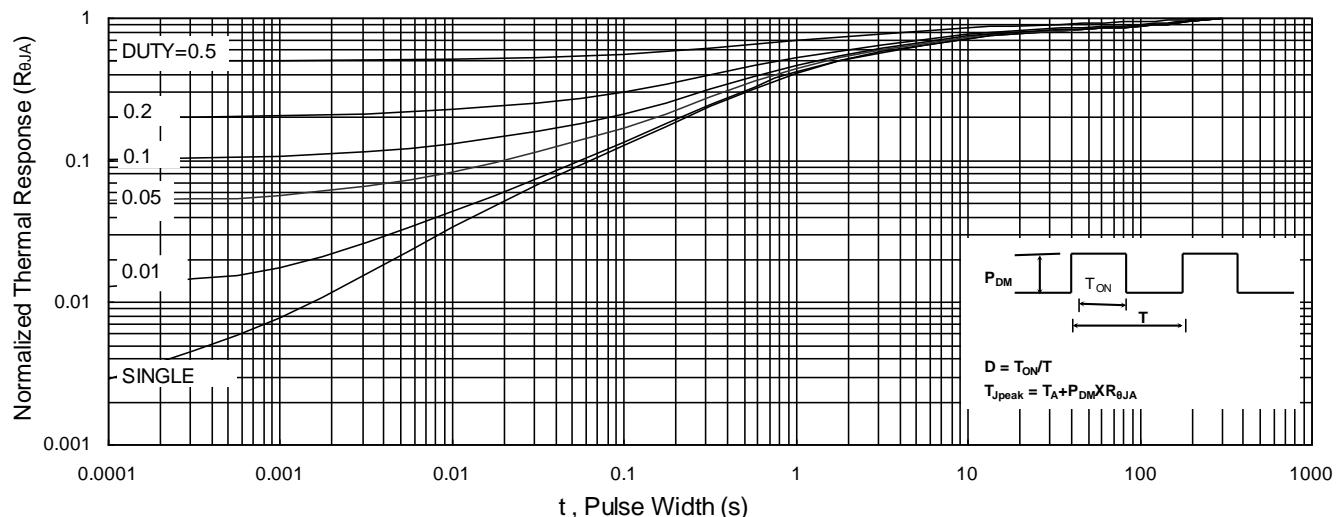


Fig.9 Normalized Maximum Transient Thermal Impedance

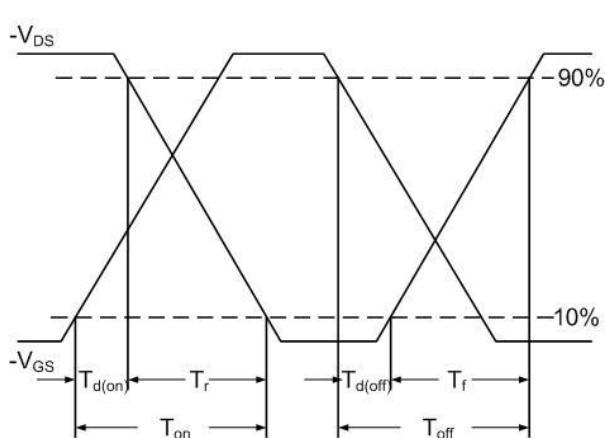


Fig.10 Switching Time Waveform

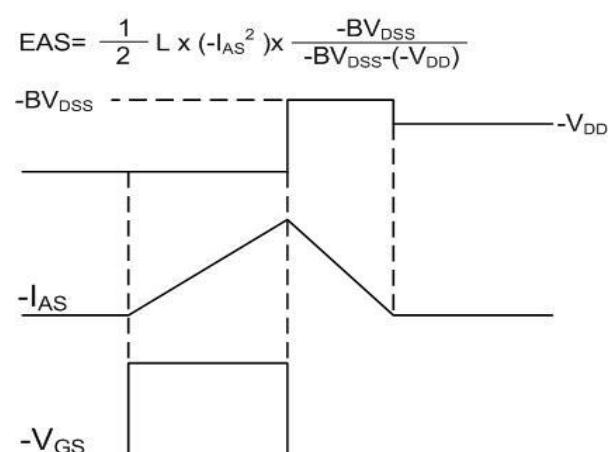


Fig.11 Unclamped Inductive Switching



Ordering Information

Part Number	Package code	Packaging
HSM3107	SOP-8	2500/Tape&Reel

